REVISIONS			
LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED
A	Make changes to the Output current test with conditions of V_{OUT} = +10 V and -10 V as specified under Table I. Changes in accordance with N.O.R. 5962-R264-97.	97-04-04	R. MONNIN
B	Make changes to 1.2 and 1.3. Redrawn. - ro	99-06-30	R. MONNIN
C	Add a dose rate footnote under paragraph 1.5 and Table I. Delete paragraphs 4.4.4.2, 4.4.4.3, and 6.7. - ro	05-10-05	R. MONNIN
D	Add device type 02. Add paragraph 3.2.3. Make clarification to footnote 1/ as specified under Table IIA. Delete paragraphs 4.4.4.1.1 and 4.4.4.2. Delete figure 2 radiation exposure circuit and references to device M requirements. - ro	15-02-25	C. SAFFLE

REV																				
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REV STATUS				REV			D	D	D	D	D	D	D	D	D	D	D	D	D	
OF SHEETS				SHEET			1	2	3	4	5	6	7	8	9	10	11	12	13	

PMIC N/A

PREPARED BY
RICK OFFICER

CHECKED BY
RAJESH PITHADIA

APPROVED BY
MICHAEL FRYE

DRAWING APPROVAL DATE
95-11-09

REVISION LEVEL
D

STANDARD MICROCIRCUIT DRAWING

THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE

AMSC N/A

DLA LAND AND MARITIME
COLUMBUS, OHIO 43218-3990
http://www.landandmaritime.dla.mil

MICROCIRCUIT, LINEAR, RADIATION HARDENED, SAMPLE AND HOLD AMPLIFIER, MONOLITHIC SILICON

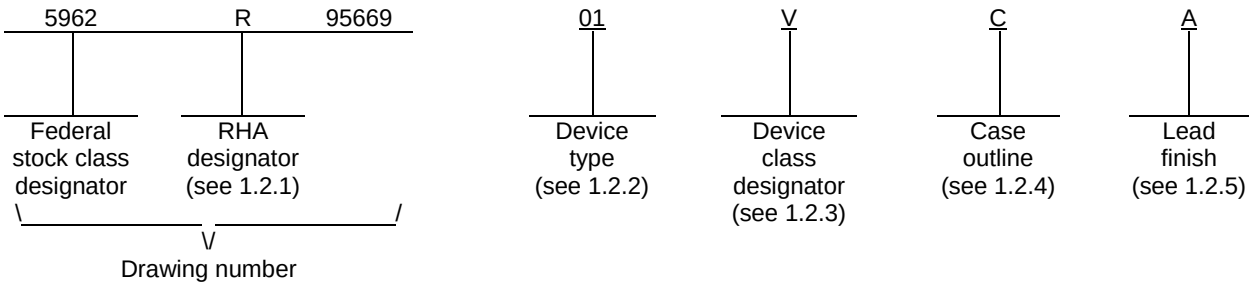
SIZE	CAGE CODE	
A	**67268**	**5962-95669**

SHEET 1 OF 13

1. SCOPE

1.1 Scope. This drawing documents two product assurance class levels consisting of high reliability (device class Q) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels is reflected in the PIN.

1.2 PIN. The PIN is as shown in the following example:



1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 Device type(s). The device type(s) identify the circuit function as follows:

Device type	Generic number	Circuit function
01	HS-2420RH	Radiation hardened, dielectrically isolated (D.I.) sample and hold amplifier
02	HS-2420EH	Radiation hardened, D.I. sample and hold amplifier

1.2.3 Device class designator. The device class designator is a single letter identifying the product assurance level as follows:

Device class	Device requirements documentation
Q or V	Certification and qualification to MIL-PRF-38535

1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	Terminals	Package style
C	GDIP1-T14 or CDIP2-T14	14	Dual in line

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V.

1.3 Absolute maximum ratings. 1/

Voltage between $+V_S$ and $-V_S$	+40 V
Differential input voltage (V_{IND})	±24 V
Digital input voltage ($\overline{S}$/H pin)	+8 V, -15 V
Output current	Short circuit protected
Maximum package dissipation (P_D) at T_A = +125°C	0.67 W 2/
Junction temperature (T_J)	+175°C
Storage temperature range	-65°C to +150°C
Lead temperature (soldering, 10 seconds)	+275°C
Thermal resistance, junction-to-case (θ_{JC})	20°C/W
Thermal resistance, junction-to-ambient (θ_{JA})	75°C/W

1.4 Recommended operating conditions.

Supply voltage range ($\pm V_S$)	±15 V
Analog input voltage	±10 V
Low input voltage (V_{IL})	0 V to 0.8 V, maximum
High input voltage (V_{IH})	2.0 V to 5.0 V
Ambient operating temperature range (T_A)	-55°C to +125°C

1.5 Radiation features:

Maximum total dose available (dose rate = 50 – 300 rads(Si)/s):	
Device type 01	100 krads(Si) 3/
Device type 02	100 krads(Si) 4/
Maximum total dose available (dose rate ≤ 0.01 rads(Si)/s):	
Device type 02	50 krads(Si) 4/
Radiation induced latch-up	No latch up 5/

1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

2/ If device power exceeds package dissipation capacity, provide heat sinking or derate linearly (the derating is based on the θ_{JA}) at the following rate : 13.3 mW/°C.

3/ Device type 01 may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effects. The radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, method 1019, condition A to a maximum total dose of 100 krads(Si) .

4/ Device type 02 radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in MIL-STD-883, method 1019, condition A to a maximum total dose of 100 krads(Si), and condition D to a maximum total dose of 50 krads(Si).

5/ Device types 01 and 02 use dielectrically isolated (DI) technology and latch up is physically not possible.

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.
MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.
MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at http://quicksearch.dla.mil or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 as specified herein, or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V.

3.2.1 Case outline. The case outline shall be in accordance with 1.2.4 herein.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.3 Timing waveforms. The timing waveforms shall be as specified on figure 2.

3.2.4 Radiation exposure circuit. The radiation exposure circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing and acquiring activity upon request.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.

TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions 1/ 2/ $-55°C \le T_A \le +125°C$ unless otherwise specified		Group A subgroups	Device type	Limits		Unit
						Min	Max	
Input offset voltage	V_{IO}		1	01,02	-4	+4	mV
			2,3		-6	+6	
			M,D,P,L,R	1		-6	+6	
Input bias current	$+I_{IB}$		1	01,02	-200	+200	nA
			2,3		-400	+400	
			M,D,P,L,R	1		-400	+400	
	$-I_{IB}$		1	01,02	-200	+200	
			2,3		-400	+400	
			M,D,P,L,R	1		-400	+400	
Input offset current	I_{IO}		1	01,02	-50	+50	nA
			2,3		-100	+100	
			M,D,P,L,R	1		-100	+100	
Open loop voltage gain	$+A_{VS}$	V_{OUT} = +10 V, R_L = 2 kΩ, C_L = 50 pF	1,2,3	01,02	25		kV/V
			M,D,P,L,R	1		25		
	$-A_{VS}$	V_{OUT} = -10 V, R_L = 2 kΩ, C_L = 50 pF	1,2,3		25		
			M,D,P,L,R	1		25		
Common mode rejection ratio	-CMRR	$+V_S$ = 25 V, $-V_S$ = -5 V, V_{OUT} = +10 V, $V_{S/H}$ = 10.8 V	1,2,3	01,02	80		dB
			M,D,P,L,R	1		80		
	+CMRR	$+V_S$ = 5 V, $-V_S$ = -25 V, V_{OUT} = -10 V, $V_{S/H}$ = 9.2 V	1,2,3		80		
			M,D,P,L,R	1		80		

See footnotes at end of table.

TABLE I. Electrical performance characteristics – Continued.

Test	Symbol	Conditions 1/ 2/ $-55°C \le T_A \le +125°C$ unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Output current	$+I_{OUT}$	V_{OUT} = +10 V, T_A = +25°C	1	01,02	+15		mA
		M,D,P,L,R	1		+10		
	$-I_{OUT}$	V_{OUT} = -10 V, T_A = +25°C	1		-15		
		M,D,P,L,R	1		-10		
Output voltage swing	$+V_{OP}$	R_L = 2 kΩ, C_L = 50 pF	1,2,3	01,02	+10		V
		M,D,P,L,R	1		+10		
	$-V_{OP}$	R_L = 2 kΩ, C_L = 50 pF	1,2,3			-10	
		M,D,P,L,R	1			-10	
Power supply current	$+I_{CC}$	T_A = +25°C	1	01,02		5.5	mA
		M,D,P,L,R	1			5.5	
	$-I_{CC}$	T_A = +25°C	1		-3.5		
		M,D,P,L,R	1		-3.5		
Power supply rejection ratio	+PSRR	$+V_S$ = 10 and 20 V, $-V_S$ = -15 and -15 V	1,2,3	01,02	80		dB
		M,D,P,L,R	1		80		
	-PSRR	$+V_S$ = 15 and 15 V, $-V_S$ = -10 and -20 V	1,2,3		80		
		M,D,P,L,R	1		80		
Digital input current	I_{IN1}	V_{IN1} = 0 V	1,2,3	01,02		800	μA
		M,D,P,L,R	1			800	
	I_{IN2}	V_{IN2} = 5 V	1,2,3			20	
		M,D,P,L,R	1			20	
Digital input voltage	V_{IL}		1,2,3	01,02		0.8	V
		M,D,P,L,R	1			0.8	
	V_{IH}		1,2,3		2.0		
		M,D,P,L,R	1		2.0		

See footnotes at end of table.

TABLE I. Electrical performance characteristics – Continued.

Test	Symbol	Conditions 1/ 2/ $-55°C \le T_A \le +125°C$ unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Drift current	I_D	V_{IN} = 0 V, R_L = 2 kΩ, C_L = 50 pF, T_A = +125°C, S/H pin at 4.0 V	2	01,02	-10	10	nA
		M,D,P,L,R	1		-10	10	
Hold mode feedthrough attenuation	VATTEN	V_{IN} = 20 V_{PP}, A_V = +1, 3/ C_L = 50 pF, R_L = 2 kΩ, f_{IN} = 50 kHz	4,5,6	01,02	70		dB
Gain bandwidth product	GBWP	V_{IN} = 100 mV_{PP}, 3/ A_V = +1, C_L = 50 pF, R_L = 2 kΩ, T_A = +25°C	4	01,02	2.5		MHz
Hold step error 4/	V_{ERR}	$V_{S/H}$ = 0 V and 4 V, $t_R(V_{S/H}) \approx$ 30 ns, T_A = +25°C	9	01,02	-20	20	mV
		M,D,P,L,R	9		-20	20	
Transient response (rise time and fall time)	TR_{TR}	V_{OUT} = 200 mV_{PP}, A_V = +1, C_L = 50 pF, R_L = 2 kΩ, T_A = +25°C	9	01,02		100	ns
		M,D,P,L,R	9			100	
	TR_{TF}		9			100	
		M,D,P,L,R	9			100	
Transient response (overshoot)	TR_{+OS}	V_{OUT} = 200 mV_{PP}, A_V = +1, C_L = 50 pF, R_L = 2 kΩ, T_A = +25°C	9	01,02		40	%
		M,D,P,L,R	9			40	
	TR_{-OS}		9			40	
		M,D,P,L,R	9			40	

See footnotes at end of table.

TABLE I. Electrical performance characteristics – Continued.

Test	Symbol	Conditions 1/ 2/ $-55°C \le T_A \le +125°C$ unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Transient response (slew rate)	TR_{+SR}	V_{OUT} = 10 V_{PP}, A_V = +1, C_L = 50 pF, R_L = 2 kΩ, T_A = +25°C	9	01,02	3.5		V/µs
		M,D,P,L,R	9		2.0		
	TR_{-SR}		9		3.5		
		M,D,P,L,R	9		2.0		
Acquisition time (0.1%)	$+t_{ACQ}$	V_{OUT} = 0 V and +10 V, 3/ A_V = +1, C_L = 50 pF, R_L = 2 kΩ, T_A = +25°C	9	01,02		4	µs
	$-t_{ACQ}$	V_{OUT} = 0 V and -10 V, 3/ A_V = +1, C_L = 50 pF, R_L = 2 kΩ, T_A = +25°C				4	
Acquisition time (0.01%)	$+t_{ACQ}$	V_{OUT} = 0 V and +10 V, 3/ A_V = +1, C_L = 50 pF, R_L = 2 kΩ, T_A = +25°C	9	01,02		6	µs
	$-t_{ACQ}$	V_{OUT} = 0 V and -10 V, 3/ A_V = +1, C_L = 50 pF, R_L = 2 kΩ, T_A = +25°C				6	

1/ Unless otherwise specified, device tested at $+V_S$ = +15 V, $-V_S$ = -15 V, V_{IL} = 0.8 V (sample), V_{IH} = 2.0 V (hold), C_H = 1000 pF, and -INPUT pin tied to OUTPUT pin. See figure 2.

2/ RHA device type 01 supplied to this drawing will meet all levels M, D, P, L, and R of irradiation. However, device type 01 is only tested at the "R" level accordance with MIL-STD-883 method 1019 condition A (see 1.5 herein). Device type 01 may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effects.

RHA device type 02 supplied to this drawing will meet all levels M, D, P, L, and R of irradiation for condition A and meet all levels M, D, P, and L for condition D. However, device type 02 is only tested at the "R" level in accordance with MIL-STD-883, method 1019, condition A and tested at the "L" level in accordance with MIL-STD-883, method 1019, condition D (see 1.5 herein).

Pre and post irradiation values are identical unless otherwise specified in table IA. When performing post irradiation electrical measurements for any RHA level, T_A = +25°C.

3/ If not tested, shall be guaranteed to the limits specified in table I herein.

4/ $V_{ERR} = V_{OUT}$ ($V_{S/H}$ = 0 V) - V_{OUT} ($V_{S/H}$ = 4 V).

Device types	01 and 02
Case outline	C
Terminal number	Terminal symbol
1	-INPUT
2	+INPUT
3	OFFSET ADJUST
4	OFFSET ADJUST
5	$-V_S$
6	NC
7	OUTPUT
8	NC
9	$+V_S$
10	NC
11	HOLD CAPACITOR
12	NC
13	GND
14	$\overline{\text{SAMPLE}}$ / HOLD CONTROL

FIGURE 1. Terminal connections.

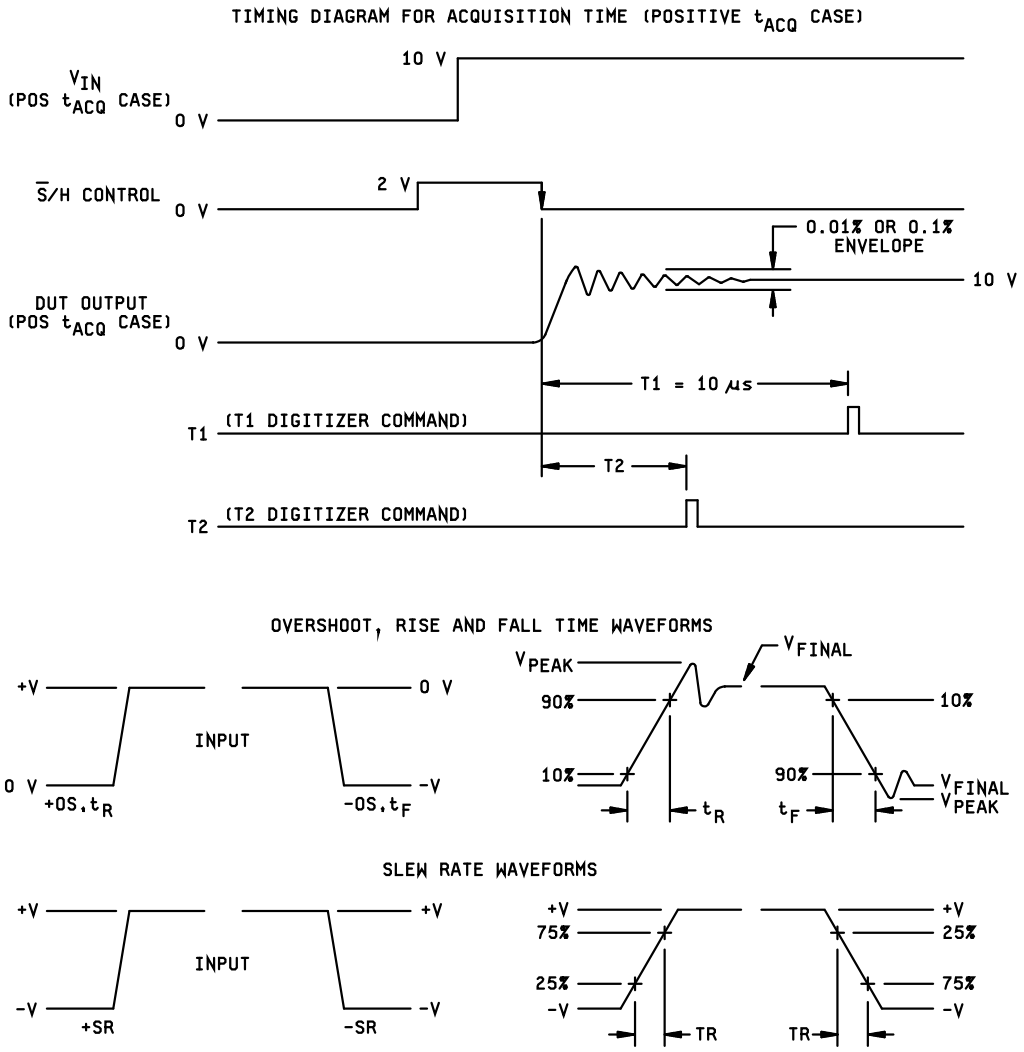


FIGURE 2. Timing waveforms.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535.

3.5.1 Certification/compliance mark. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535.

3.6 Certificate of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). The certificate of compliance submitted to DLA Land and Maritime-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein.

3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 shall be provided with each lot of microcircuits delivered to this drawing.

4. VERIFICATION

4.1 Sampling and inspection. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection.

4.2.1 Additional criteria for device classes Q and V.

a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.

b. Interim and final electrical test parameters shall be as specified in table IIA herein.

c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 Conformance inspection. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections, and as specified herein.

4.4.1 Group A inspection.

a. Tests shall be as specified in table IIA herein.

b. Subgroups 7, 8, 10, and 11 in table I, method 5005 of MIL-STD-883 shall be omitted.

TABLE IIA. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class Q	Device class V
Interim electrical parameters (see 4.2)	1,9	1,9
Final electrical parameters (see 4.2)	1,2,3,4,5, 1/ 6,9	1,2,3, 1/ 2/ 4,5,6,9
Group A test requirements (see 4.4)	1,2,3,4,5,6,9	1,2,3,4,5,6,9
Group C end-point electrical parameters (see 4.4)	1,2,3	1,2,3 2/
Group D end-point electrical parameters (see 4.4)	1	1
Group E end-point electrical parameters (see 4.4)	1,2,3,9	1,2,3,9

1/ For device class Q, PDA applies to subgroup 1.
For device class V, PDA applies to subgroup 1 and deltas.
2/ Delta limits as specified in table IIB shall be required where specified, and the delta limits shall be completed with reference to the previous electrical parameters.

TABLE IIB. Burn-in and operating life test delta parameters. T_A = +25°C.

Parameters	Symbol	Device types	Limit
Input offset voltage	V_{IO}	01,02	±2 mV
Input bias current	I_{IB}	01,02	±75 nA
Input offset current	I_{IO}	01,02	±75 nA

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.2.1 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.

4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

a. End-point electrical parameters shall be as specified in table IIA herein.

b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C ±5°C, after exposure, to the subgroups specified in table IIA herein.

4.4.4.1 Total dose irradiation testing. Total dose irradiation testing shall be performed in accordance with MIL-STD-883 method 1019, condition A and as specified herein for device types 01 and 02. In addition, for device type 02, a low dose rate test shall be performed in accordance with MIL-STD-883 method 1019, condition D and as specified herein.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor prepared specification or drawing.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform DLA Land and Maritime when a system application requires configuration control and which SMD's are applicable to that system. DLA Land and Maritime will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DLA Land and Maritime-VA, telephone (614) 692-8108.

6.4 Comments. Comments on this drawing should be directed to DLA Land and Maritime-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0540.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in MIL-HDBK-103 and QML-38535. The vendors listed in MIL-HDBK-103 and QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DLA Land and Maritime-VA and have agreed to this drawing.

STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 15-02-25

Approved sources of supply for SMD 5962-95669 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DLA Land and Maritime-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DLA Land and Maritime maintains an online database of all current sources of supply at http://www.landandmaritime.dla.mil/Programs/Smcr/.

Standard microcircuit drawing PIN 1/	Vendor CAGE number	Vendor similar PIN 2/
5962R9566901VCA	3/	HS1-2420RH-Q
5962R9566901VCC	3/	HS1B-2420RH-Q
5962R9566902VCC	34371	HS1B-2420EH-Q

1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.
3/ Not available from an approved source of supply.

Vendor CAGE number	Vendor name and address
34371	Intersil Corporation 1001 Murphy Ranch Road Milpitas, CA 95035-6803

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.